

Application Number 10/626,212  
Amendment dated 10 November 2005  
Reply to Office Action of 22 August 2005

Amendments to the Specification

Please add the following new paragraph after paragraph [0107]:

[0107.1] In one embodiment, a transistor gate stack is formed by first forming a gate dielectric over a semiconductor substrate. The gate dielectric is then exposed to a source of nitrogen excited species. This exposure causes less than about 10 atomic % nitrogen at a depth of greater than about 10 Å from an upper surface of the gate dielectric to be incorporated into the gate dielectric. A silicon-containing gate electrode is then deposited over the gate dielectric.